

SPTECH Silicon NPN Power Transistor

BU931T

DESCRIPTION

- High Voltage
- DARLINGTON

APPLICATIONS

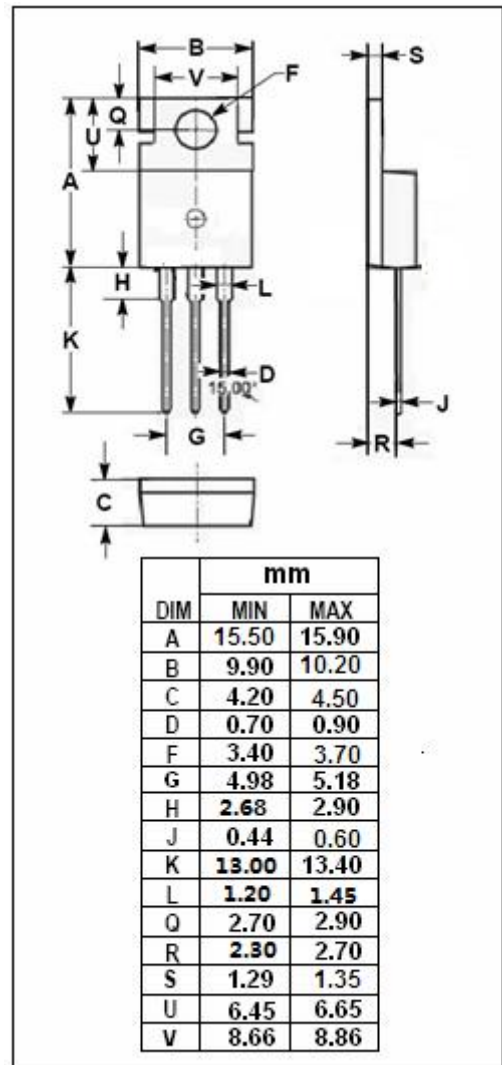
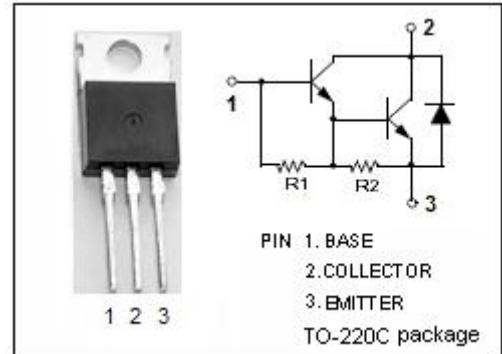
- High ruggedness electronic ignitions
- High voltage ignition coil driver

ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	500	V
V _{CEO}	Collector-Emitter Voltage	400	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current	10	A
I _{CM}	Collector Current-peak	15	A
I _B	Base Current	1	A
I _{BM}	Base Current-peak	5	A
P _C	Collector Power Dissipation @T _c =25°C	125	W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-65~150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	1.2	°C/W



ELECTRICAL CHARACTERISTICS

T_c=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	I _C = 50mA; I _B = 0	400			V
V _{CE(sat)-1}	Collector-Emitter Saturation Voltage	I _C = 7A; I _B = 70mA			1.6	V
V _{CE(sat)-2}	Collector-Emitter Saturation Voltage	I _C = 8 A; I _B = 100mA			1.8	V
V _{BE(sat)-1}	Base-Emitter Saturation Voltage	I _C = 7A; I _B = 70mA			2.2	V
V _{BE(sat)-2}	Base-Emitter Saturation Voltage	I _C = 8 A; I _B = 100mA			2.4	V
I _{CES}	Collector Cutoff Current	V _{CE} = 500V; V _{BE} = 0 V _{CE} = 500V; V _{BE} = 0; T _j = 125°C			0.1 0.5	mA
I _{CEO}	Collector Cutoff Current	V _{CE} = 450V; I _B = 0 V _{CE} = 450V; I _B = 0; T _j = 125°C			0.1 0.5	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0			20	mA
h _{FE}	DC Current Gain	I _C = 5A ; V _{CE} = 10V	300			
V _{ECF}	C-E Diode Forward Voltage	I _F = 10A			2.5	V